



S/N 09/883795

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Leonard Forbes et al. Examiner: Theresa Doan  
Serial No.: 09/883795 Group Art Unit: 2814  
Filed: June 18, 2001 Docket: 303.355US4  
Title: METHOD OF FORMING A DEVICE WITH A GALLIUM NITRIDE OR  
GALLIUM ALUMINUM NITRIDE GATE

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**COMMUNICATION CONCERNING RELATED APPLICATION(S)**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date</u>	<u>Attorney Docket</u>	<u>Title</u>
08/903452	July 29, 1997	303.324US1	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
09/256643	February 23, 1999	303.324US2	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
09/652420	August 31, 2000	303.324US3	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
09/691004	October 18, 2000	303.324US4	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
08/903486	July 29, 1997	303.326US1	SILICON CARBIDE GATE TRANSISTOR

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Page 2

Dkt: 303.355US4

09/259870	March 1, 1999	303.326US2	FABRICATION OF SILICON CARBIDE GATE TRANSISTOR
08/902132 5886368	July 29, 1997	303.353US1	TRANSISTOR WITH SILICON OXYCARBIDE GATE AND METHODS OF FABRICATION AND USE
09/138294 6309907	August 21, 1998	303.353US2	TRANSISTOR WITH SILICON OXYCARBIDE GATE AND METHODS OF FABRICATION AND USE
08/902843	July 29, 1997	303.354US1	DEAPROM HAVING AMORPHOUS SILICON CARBIDE GATE INSULATOR
09/135413	August 14, 1998	303.354US2	METHOD FOR OPERATING A MEMORY DEVICE HAVING AN AMORPHOUS SILICON CARBIDE GATE INSULATOR
09/134713	August 14, 1998	303.354US3	DEAPROM HAVING AMORPHOUS SILICON CARBIDE GATE INSULATOR
09/140978 6307775	August 27, 1998	303.355US2	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
10/047181	October 23, 2001	303.355US5	MEMORY DEVICE WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
08/902133	July 29, 1997	303.356US1	MEMORY DEVICE
10/231687	August 29, 2002	303.356US2	DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ ONLY MEMORY DEVICE
08/903453	July 29, 1997	303.378US1	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS

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Page 3

Dkt: 303.355US4

09/258467	February 26, 1999	303.378US2	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS
09/650553	August 30, 2000	303.378US3	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS
10/461593	June 11, 2003	303.356US3	DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ ONLY MEMORY DEVICE

Respectfully submitted,


LEONARD FORBES ET AL.

By Applicants' Representatives,

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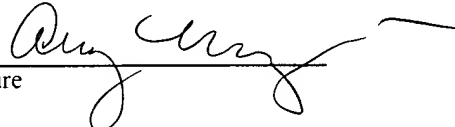
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Robert E. Mates  
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Examiner: Theresa Doan



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Due Date: January 22, 2004  
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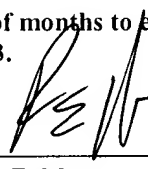
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- ☒ A return postcard.
- ☒ An Amendment and Response (16 Pages).
- ☒ A Communication Concerning Related Applications (3 pgs.).
- ☒ A Supplemental Information Disclosure Statement (1 pg.), Form 1449 (1 pg.), and copies of 13 cited documents.
- ☒ A check in the amount of \$180.00 to cover the fee for consideration of Information Disclosure Statement under 97(c).
- ☒ Terminal Disclaimer (3 pgs.).
- ☒ A check in the amount of \$110.00 to cover the fee required to file the Terminal Disclaimer.
- ☒ An Appointment of Associate Representative (1 pg.).

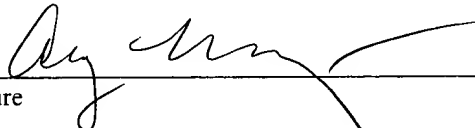
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SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.  
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(GENERAL)